



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>



## NTE2672 Silicon NPN Transistor High Gain, Low Frequency, General Purpose Amp TO92 Type Package

### Features:

- High DC Current Gain:  $h_{FE} = 800$  to  $3200$
- Low Collector–Emitter Saturation Voltage:  $V_{CE(sat)} = 0.5V$  Max
- High Collector–Base Voltage:  $V_{EBO} \geq 15V$

### Applications:

- Low Frequency, General Purpose Amp
- Various Drivers
- Muting Circuit

### Absolute Maximum Ratings: ( $T_A = +25^\circ C$ unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	60V
Collector–Emitter Voltage, $V_{CEO}$ .....	50V
Emitter–Base Voltage, $V_{EBO}$ .....	15V
Collector Current, $I_C$	
Continuous .....	200mA
Pulsed .....	300mA
Base Current, $I_B$ .....	40mA
Collector Dissipation, $P_C$ .....	600mW
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C

### Electrical Characteristics: ( $T_A = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	$I_{CBO}$	$V_{CB} = 40V, I_E = 0$	-	-	0.1	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB} = 10V, I_C = 0$	-	-	0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 5V, I_C = 10mA$	800	1500	3200	
		$V_{CE} = 5V, I_C = 100mA$	600	-	-	
Gain–Bandwidth Product	$f_T$	$V_{CE} = 10V, I_C = 10mA$	-	250	-	MHz
Common Base Output Capacitance	$c_{ob}$	$V_{CB} = 10V, f = 1MHz$	-	4.0	-	pF
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 2mA$	-	0.12	0.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 2mA$	-	0.85	1.2	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60	-	-	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	50	-	-	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	15	-	-	V

